

## Correction to Effective Cleaning of Hexagonal Boron Nitride for Graphene Devices

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There are typographical errors in the captions to Figures 4 and 5. In the caption to Figure 4, lines 11–12, “(e) after treatment in Ar/H<sub>2</sub> at 350 °C, (f) after treatment in Ar/H<sub>2</sub> at 500 °C” should instead be “(e) after treatment in Ar/O<sub>2</sub> at 350 °C, (f) after treatment in Ar/O<sub>2</sub> at 500 °C”. Similarly, in the caption to Figure 5, lines 8–9, “(e) after treatment in Ar/H<sub>2</sub> at 350 °C, and (f) after subsequent heat treatment in Ar/H<sub>2</sub> at 500 °C” should instead be “(e) after treatment in Ar/O<sub>2</sub> at 350 °C, and (f) after subsequent heat treatment in Ar/O<sub>2</sub> at 500 °C”. The passages in the main text that refer to these figures provide the correct information.